

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Salvatore Lombardo et al.  
Filed : July 7, 2003  
For : A GERMANIUM IMPLANTED HBT BIPOLAR  
TRANSISTOR

Docket No. : 856063.547D1  
Date : July 7, 2003

Mail Stop Patent Application  
Commissioner for Patents  
Washington, DC 20231

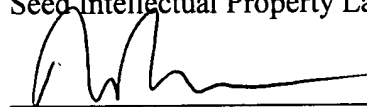
INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the 13 references set forth on the attached Form PTO-1449. This application relies, under 35 U.S.C. § 120, on the earlier filing date of prior Application No. 09/724,563 filed on November 27, 2000 and 09/087,398, filed May 29, 1998. The references listed on the attached Form PTO-1449 were submitted to and/or cited by the Patent and Trademark Office in this prior application and, therefore, are not required to be provided in this application. If the Examiner wishes, copies will be provided upon request. As to any reference supplied, applicants do not admit that it is "prior art" under 35 U.S.C. §§ 102 or 103, and specifically reserve the right to traverse or antedate any such reference, as by a showing under 37 C.F.R. § 1.131 or other method. Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information they are aware of which is believed relevant to the examination of the above-identified application, applicants believe that their invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,  
Salvatore Lombardo et al.  
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FORM PTO-1449 (REV.7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. <b>856063.547D1</b>		APPLICATION NO.	
<b>INFORMATION DISCLOSURE STATEMENT</b> <i>(Use several sheets if necessary)</i>				APPLICANTS <b>Salvatore Lombardo et al.</b>			
				FILING DATE <b>July 7, 2003</b>		GROUP ART UNIT	
<b>U.S. PATENT DOCUMENTS</b>							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
AA	4,343,080	08/10/82	Hataishi et al.	29	571		
AB	5,028,557	07/02/91	Tsai et al.	437	59		
AC	5,126,278	06/30/92	Kodaira	437	24		
AD	5,635,423	06/03/97	Huang et al.	437	195		
AE	5,659,201	08/19/97	Wolleson	257	758		
AF	5,712,177	01/17/98	Kaushik et al.	437	42		
AG	5,753,967	05/19/98	Lin	257	635		
AH	5,643,825	07/01/97	Gardner et al.	437	70		
AI	5,814,555	09/29/98	Bandyopadhyay et al.	438	619		
AJ	5,821,149	10/13/98	Schuppen et al.	438	312		
AK	5,847,460	12/08/98	Liou et al.	257	751		
<b>FOREIGN PATENT DOCUMENTS</b>							
	DOCUMENT NUMBER	DATE	COUNTRY			TRANSLATION YES NO	
AL	03-292740	12/24/91	Japan				
AM	0697716A2	02/21/96	EP				
AN							
<b>OTHER PRIOR ART</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
AO	S. Wolf et al., "Silicon Processing for the VLSI Era V1" - <i>Process Technology</i> , 1986, pp 182-183.						
AP	Gomi et al., "A Sub-30psec Si Bipolar LSI Technology," in International Electron Devices Meeting, San Francisco, December 11-14, 1988, <i>Institute of Electrical and Electronics Engineers</i> , No. 1988, pp 744-747, 1988.						
AQ	Lombardo, S. et al., "Ge Ion Implantation in Si for the Fabrication of Si/Ge Si Heterojunction Transistors," <i>Materials Chemistry and Physics</i> , 46(2-3), pp. 156-160, 1996.						
EXAMINER				DATE CONSIDERED			
* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).							